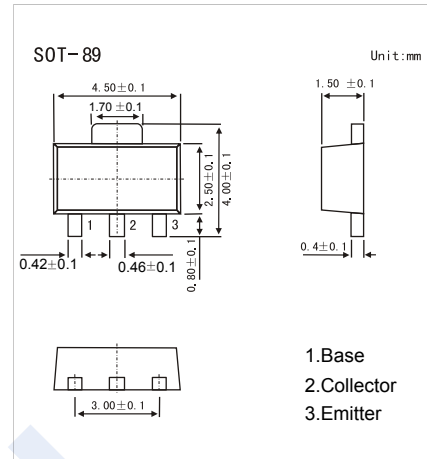


PNP Transistors

2SB1427

■ Features

- Low saturation voltage,
- Excellent DC current gain characteristics.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-20	V
Collector - Emitter Voltage	V _{CEO}	-20	
Emitter - Base Voltage	V _{EB0}	-6	
Collector Current - Continuous	I _C	-2	A
Collector Current - Pulse	I _{CP}	-3	
Collector Power Dissipation	P _C	0.5	W
		2	
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 uA, I _E =0	-20			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, I _B =0	-20			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 uA, I _C =0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -16V, I _E =0			-0.5	uA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _C =0			-0.5	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1 A, I _B =-50 mA			-0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-1 A, I _B =-50 mA			-1.2	
DC current gain	h _{FE}	V _{CE} = -6V, I _C = -500 mA	390		820	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz		30		pF
Transition frequency	f _T	V _{CE} = -10V, I _E = 10 mA, f=100MHz		90		MHz

■ Marking

Marking	BJ *
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PNP Transistors

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■ Typical Characteristics

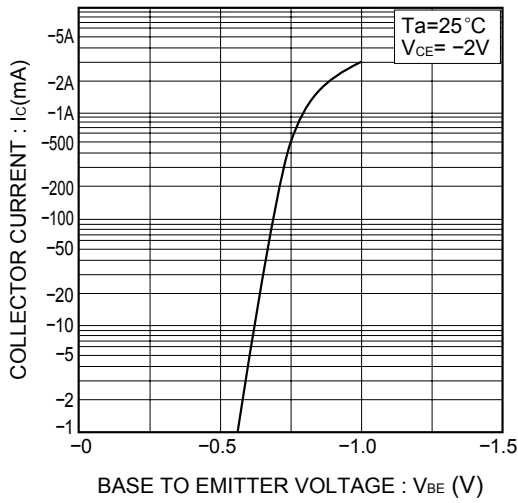


Fig.1 Grounded emitter propagation characteristics

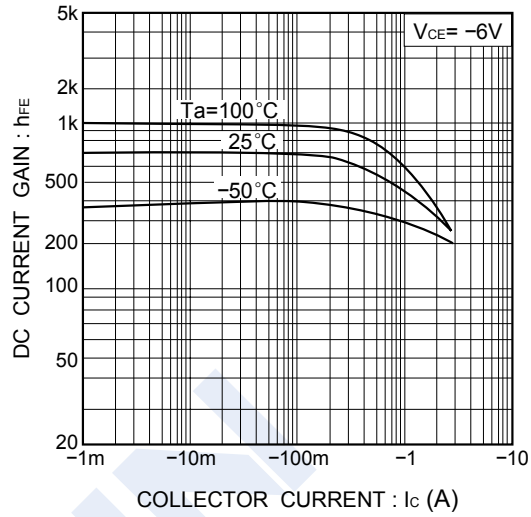


Fig.2 DC current gain vs. collector current

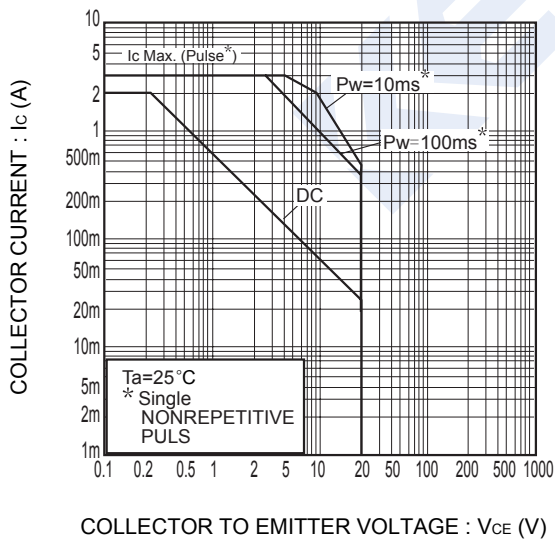


Fig.4 Safe Operating area

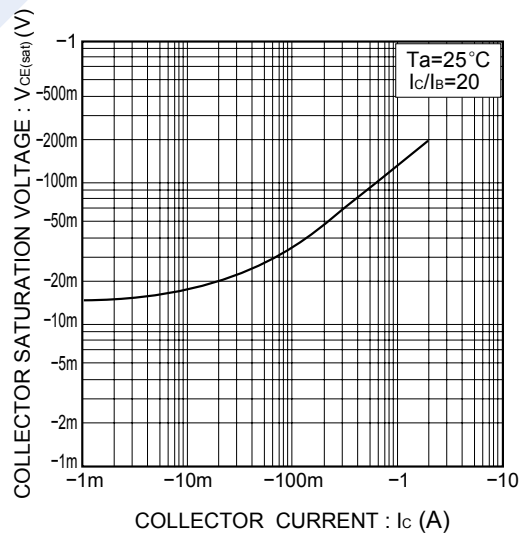


Fig.3 Collector-emitter saturation voltage vs. collector current